

Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

[Fairchild Semiconductor](#)

[ISL9R8120P2](#)

For any questions, you can email us directly:

sales@integrated-circuit.com

FAIRCHILD
SEMICONDUCTOR®

June 2002

ISL9R8120P2, ISL9R8120S3S

Features

- Stealth Recovery $t_{rr} = 300$ ns (@ $I_F = 8$ A)
- Max Forward Voltage, $V_F = 3.3$ V (@ $T_C = 25^\circ\text{C}$)
- 1200 V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS compliant

Applications

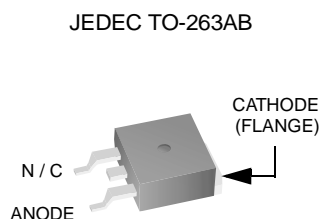
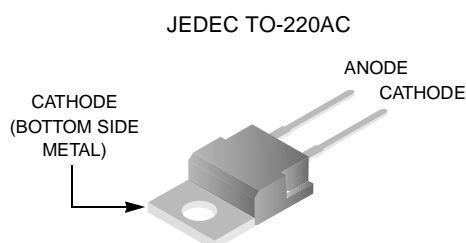
- Switch Mode Power Supplies
- Hard Switched PFC Boost Diode
- UPS Free Wheeling Diode
- Motor Drive FWD
- SMPS FWD
- Snubber Diode

8 A, 1200 V, STEALTH™ Diode

The ISL9R8120P2, ISL9R8120S3S is a STEALTH™ diode optimized for low loss performance in high frequency hard switched applications. The STEALTH™ family exhibits low reverse recovery current ($I_{RM(REC)}$) and exceptionally soft recovery under typical operating conditions. This device is intended for use as a free wheeling or boost diode in power supplies and other power switching applications. The low $I_{RM(REC)}$ and short t_a phase reduce loss in switching transistors. The soft recovery minimizes ringing, expanding the range of conditions under which the diode may be operated without the use of additional snubber circuitry. Consider using the STEALTH™ diode with an SMPS IGBT to provide the most efficient and highest power density design at lower cost.

Package

Symbol



Device Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
V_{RWM}	Working Peak Reverse Voltage	1200	V
V_R	DC Blocking Voltage	1200	V
$I_{F(AV)}$	Average Rectified Forward Current ($T_C = 105^\circ\text{C}$)	8	A
I_{FRM}	Repetitive Peak Surge Current (20 kHz Square Wave)	16	A
I_{FSM}	Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60 Hz)	100	A
P_D	Power Dissipation	71	W
E_{AVL}	Avalanche Energy (1 A, 40 mH)	20	mJ
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering		$^\circ\text{C}$
T_{PKG}	Leads at 0.063 in (1.6 mm) from Case for 10 s Package Body for 10s, See Application Note AN-7528	300 260	$^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Package Marking and Ordering Information

Device Marking	Device	Package	Tape Width	Quantity
R8120P2	ISL9R8120P2	TO-220AC	N/A	50
R8120S3S	ISL9R8120S3S	TO-263AB	24mm	800

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
--------	-----------	-----------------	-----	-----	-----	------

Off State Characteristics

I_R	Instantaneous Reverse Current	$V_R = 1200\text{ V}$	$T_C = 25^\circ\text{C}$	-	-	100	μA
			$T_C = 125^\circ\text{C}$	-	-	1.0	mA

On State Characteristics

V_F	Instantaneous Forward Voltage	$I_F = 8\text{ A}$	$T_C = 25^\circ\text{C}$	-	2.8	3.3	V
			$T_C = 125^\circ\text{C}$	-	2.7	3.1	V

Dynamic Characteristics

C_J	Junction Capacitance	$V_R = 10\text{ V}, I_F = 0\text{ A}$	-	30	-	pF
-------	----------------------	---------------------------------------	---	----	---	-------------

Switching Characteristics

t_{rr}	Reverse Recovery Time	$I_F = 1\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}, V_R = 30\text{ V}$	-	25	32	ns
		$I_F = 8\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}, V_R = 30\text{ V}$	-	35	44	ns
t_{rr}	Reverse Recovery Time	$I_F = 8\text{ A},$ $dI_F/dt = 200\text{ A}/\mu\text{s},$ $V_R = 780\text{ V}, T_C = 25^\circ\text{C}$	-	300	-	ns
I_{rr}	Reverse Recovery Current		-	4.3	-	A
Q_{rr}	Reverse Recovered Charge		-	525	-	nC
t_{rr}	Reverse Recovery Time		-	375	-	ns
S	Softness Factor (t_b/t_a)	$I_F = 8\text{ A},$ $dI_F/dt = 200\text{ A}/\mu\text{s},$ $V_R = 780\text{ V},$ $T_C = 125^\circ\text{C}$	-	9	-	-
I_{rr}	Reverse Recovery Current		-	5.5	-	A
Q_{rr}	Reverse Recovered Charge		-	1.1	-	μC
t_{rr}	Reverse Recovery Time		-	200	-	ns
S	Softness Factor (t_b/t_a)	$I_F = 8\text{ A},$ $dI_F/dt = 1000\text{ A}/\mu\text{s},$ $V_R = 780\text{ V},$ $T_C = 125^\circ\text{C}$	-	5.5	-	-
I_{rr}	Reverse Recovery Current		-	11	-	A
Q_{rr}	Reverse Recovered Charge		-	1.2	-	μC
dI_M/dt	Maximum dI/dt during t_b		-	310	-	$\text{A}/\mu\text{s}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case	TO-220, TO-263	-	-	1.75	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	TO-220, TO-263	-	-	62	$^\circ\text{C}/\text{W}$

Typical Performance Curves

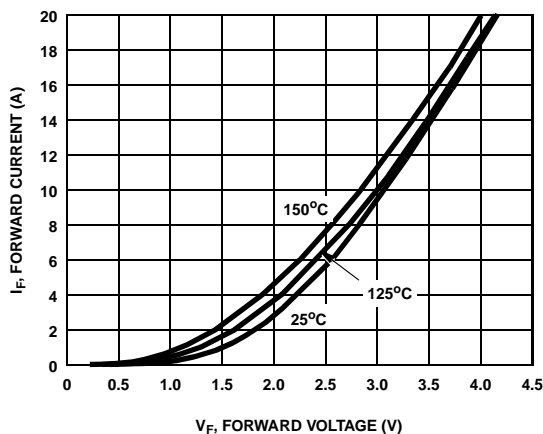


Figure 1. Forward Current vs Forward Voltage

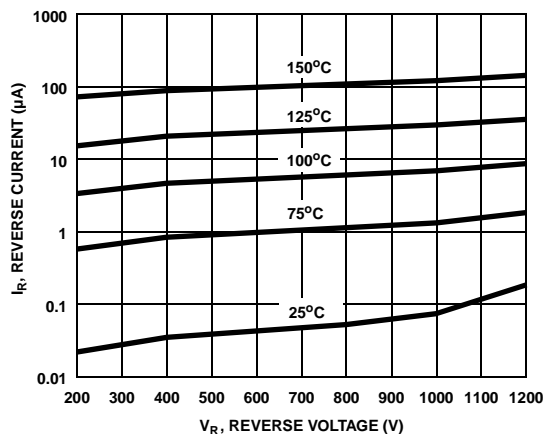


Figure 2. Reverse Current vs Reverse Voltage

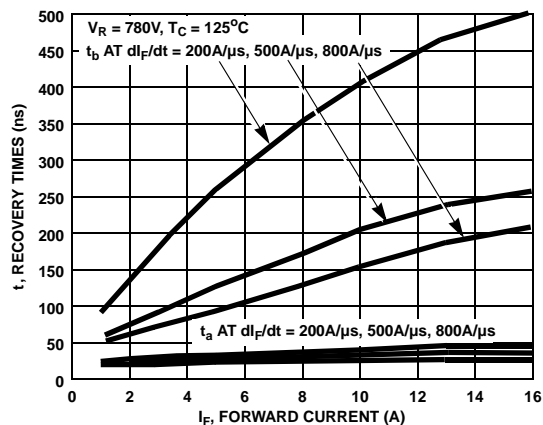


Figure 3. t_a and t_b Curves vs Forward Current

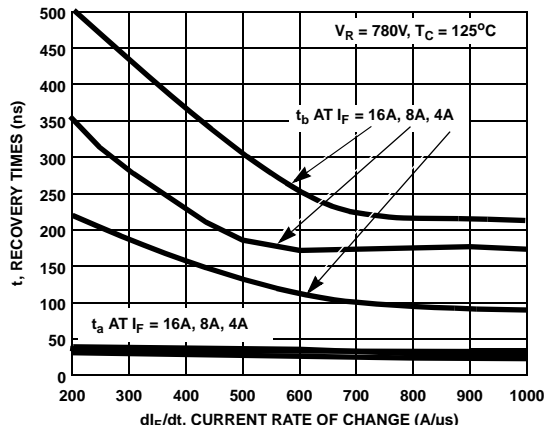


Figure 4. t_a and t_b Curves vs dl_F/dt

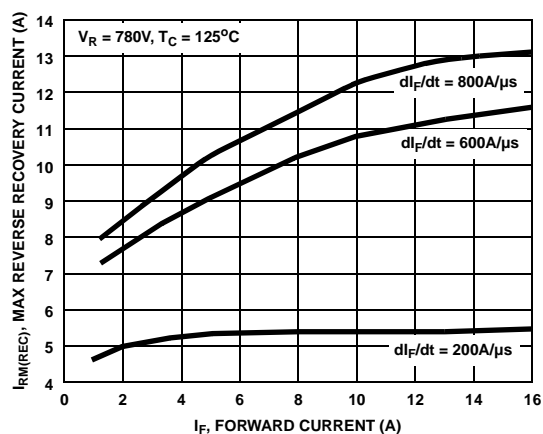


Figure 5. Maximum Reverse Recovery Current vs Forward Current

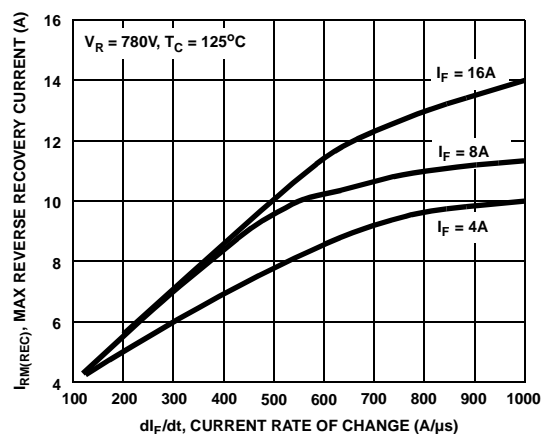


Figure 6. Maximum Reverse Recovery Current vs dl_F/dt

Typical Performance Curves (Continued)

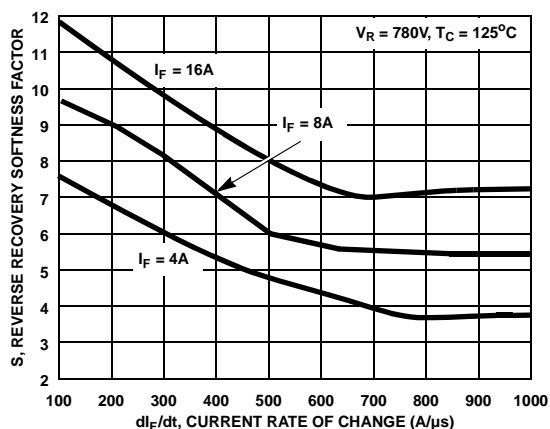


Figure 7. Reverse Recovery Softness Factor vs dI_F/dt

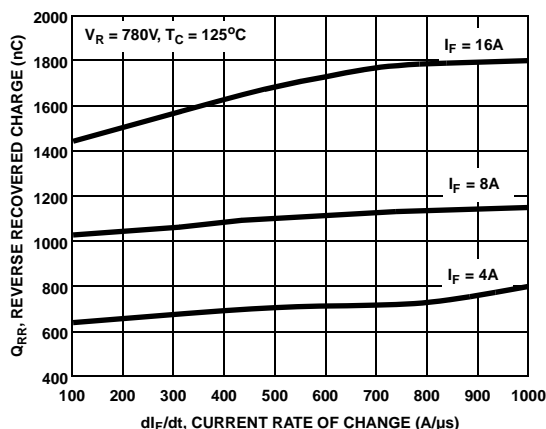


Figure 8. Reverse Recovered Charge vs dI_F/dt

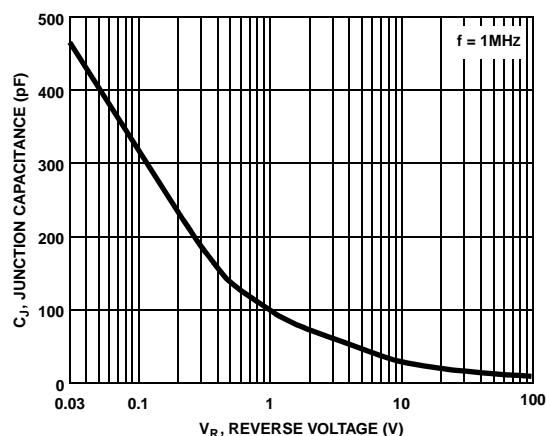


Figure 9. Junction Capacitance vs Reverse Voltage

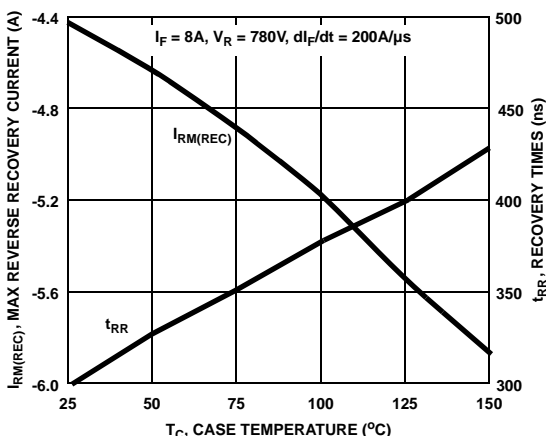


Figure 10. Reverse Recovery Current and Times vs Case Temperature

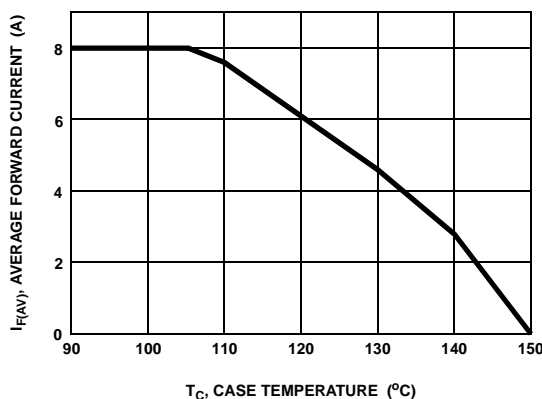


Figure 11. DC Current Derating Curve

Typical Performance Curves (Continued)

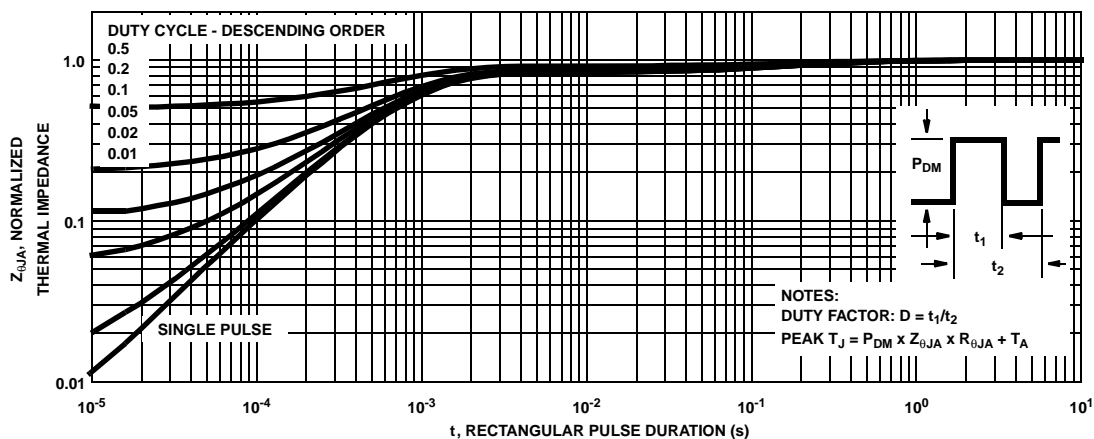


Figure 12. Normalized Maximum Transient Thermal Impedance

Test Circuit and Waveforms

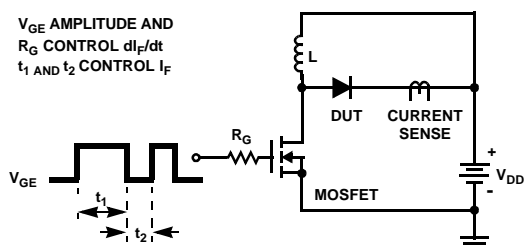


Figure 13. t_{rr} Test Circuit

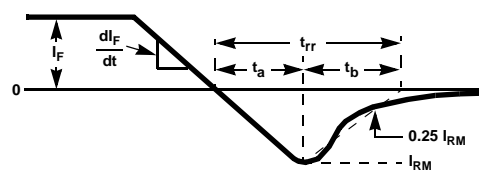


Figure 14. t_{rr} Waveforms and Definitions

$I = 1A$
 $L = 40mH$
 $R < 0.1\Omega$
 $V_{DD} = 50V$
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)} / (V_{R(AVL)} - V_{DD})]$
 $Q_1 = IGBT (BV_{CES} > DUT V_{R(AVL)})$

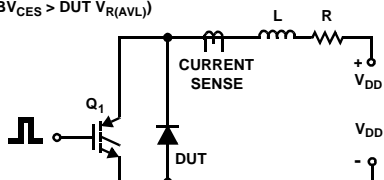


Figure 15. Avalanche Energy Test Circuit

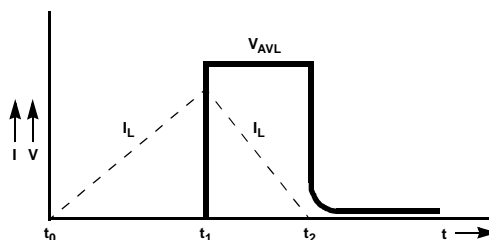


Figure 16. Avalanche Current and Voltage Waveforms

ISL9R8120P2, ISL9R8120S3S 8 A, 1200 V, STEALTH™ Diode



TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

2Cool™
AccuPower™
AX-CAP®*
BitSiC™
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
DEUXPEED®
Dual Cool™
EcoSPARK®
EfficientMax™
ESBC™
F®
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FETBench™

FPS™
F-PFS™
FRFET®
Global Power Resource™
GreenBridge™
Green FPS™
Green FPS™ e-Series™
Gmax™
GTO™
IntelliMAX™
ISOPLANAR™
Making Small Speakers Sound Louder and Better™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MicroPak2™
MillerDrive™
MotionMax™
mWSaver™
OptoHit™
OPTOLOGIC®
OPTOPLANAR®

®
PowerTrench®
PowerXS™
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
™
Saving our world, 1mW/W/kW at a time™
SignalWise™
SmartMax™
SMART START™
Solutions for Your Success™
SPM®
STEALTH™
SuperFET®
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS™
SyncFET™

Sync-Lock™
 SYSTEM GENERAL®
TinyBoost™
TinyBuck™
TinyCalc™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
TranSiC™
TriFault Detect™
TRUECURRENT®*
µSerDes™
 SerDes®
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
XS™

* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I64